

isc Silicon PNP Power Transistors

2SB656

DESCRIPTION

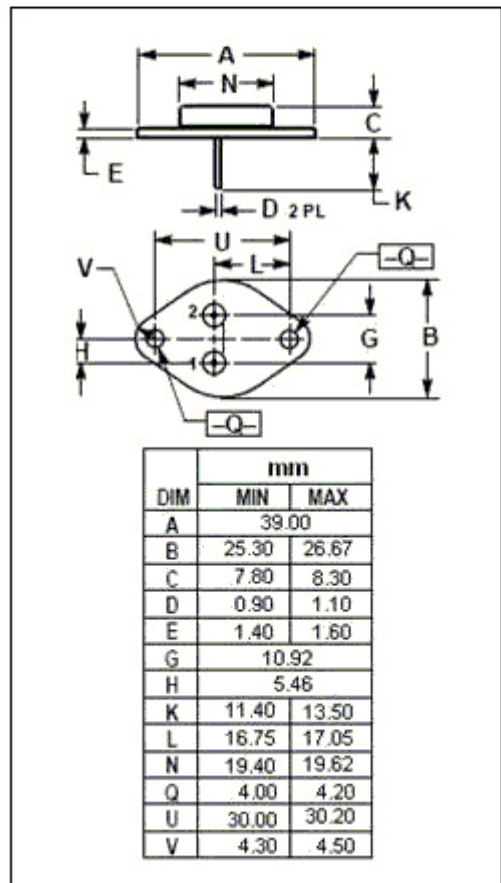
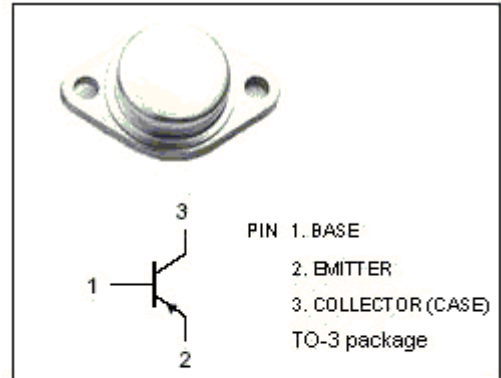
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -160V(\text{Min})$
- High Power Dissipation-
: $P_C = 125W(\text{Max})@T_C=25^\circ\text{C}$
- Complement to Type 2SD676

APPLICATIONS

- Designed for low frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-160	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-12	A
I_{CM}	Collector Current-Peak	-20	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	125	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



isc Silicon PNP Power Transistors**2SB656****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -50mA; R _{BE} = ∞	-160			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -5mA; I _C = 0	-5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -6A; I _B = -0.6A			-2.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -1A; V _{CE} = -5V			-1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -120V; I _E = 0			-0.1	mA
h _{FE-1}	DC Current Gain	I _C = -1A; V _{CE} = -5V	60		200	
h _{FE-2}	DC Current Gain	I _C = -6A; V _{CE} = -5V	20			
f _T	Current-Gain—Bandwidth Product	I _C = -1A; V _{CE} = -5V		22		MHz

◆ **h_{FE} Classifications**

B	C
60-120	100-200